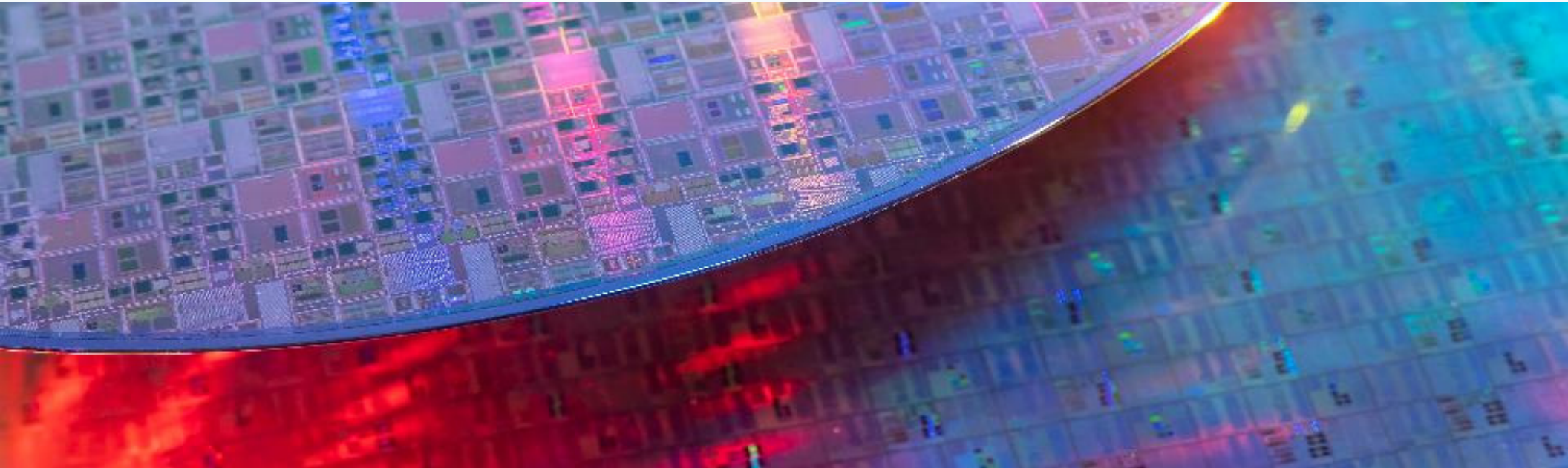
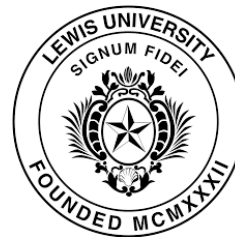


# Flucto-Clean® – A Novel Approach to Post-CMP Cleaning



**Ara Philipossian and Yasa Sampurno, (Araca, Inc.)**  
**Jason Keleher (Lewis University)**

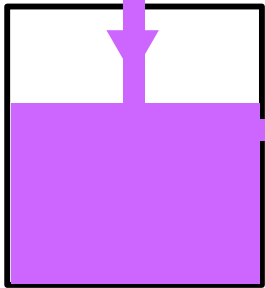


## Traditional PVA Brush Scrubbing

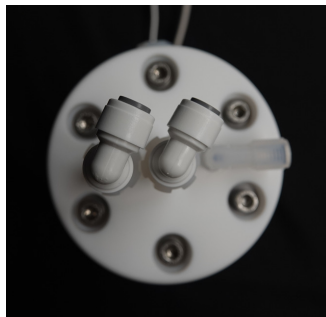
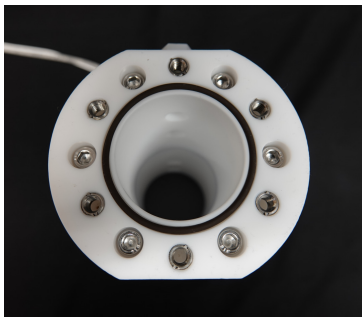
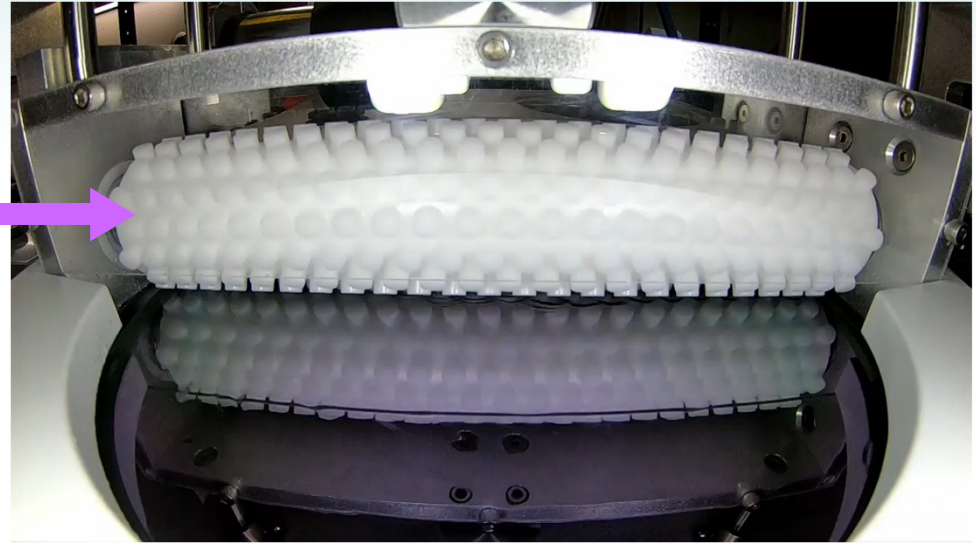
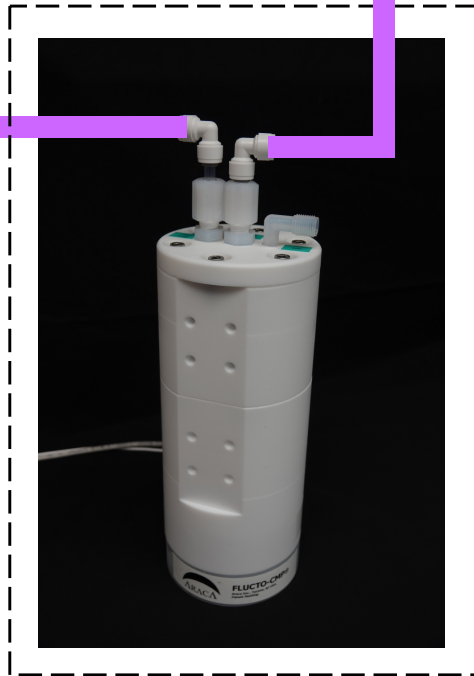
- PVA brush scrubbing continues to be the *de facto* method for advanced-node post-CMP cleans.
- Based on direct contact between a rotating spongy PVA brush and the wafer surface in the presence of certain chemically-active agents.
  - ❖ Particle is first chemically “loosened up” from the wafer surface (via passivation layer formation, charge engineering, charge flipping, and shear force management)
  - ❖ Particle is then adsorbed on brush asperities
  - ❖ Wafer and brush rotations, and brush pressure, in the presence of a cleaning fluid dislodge and carry the particle away from the wafer surface
  - ❖ Megasonic agitation is often used for improved PRE – But at the wafer level
- Factors like megasonic power at the brush-wafer interface, pressure, tool kinematics, physical and **chemical properties** of the brush and the **cleaning fluid**, wafer surface condition, cleaning time, and magnitude of the shear forces are essential for high PRE.

# The NEW Idea Behind Our Patent-Pending Flucto-Clean®

OPTIONAL  
sono-activatable  
additive



standard post-CMP  
cleaning solution



OFF-THE-SHELF  
POST-CMP CLEANING  
SOLUTION **PLUS** A  
SONO-ACITIVATABLE  
ADDITIVE FLOWS  
INTO THE  
FLUCTO-CLEAN®  
REACTOR

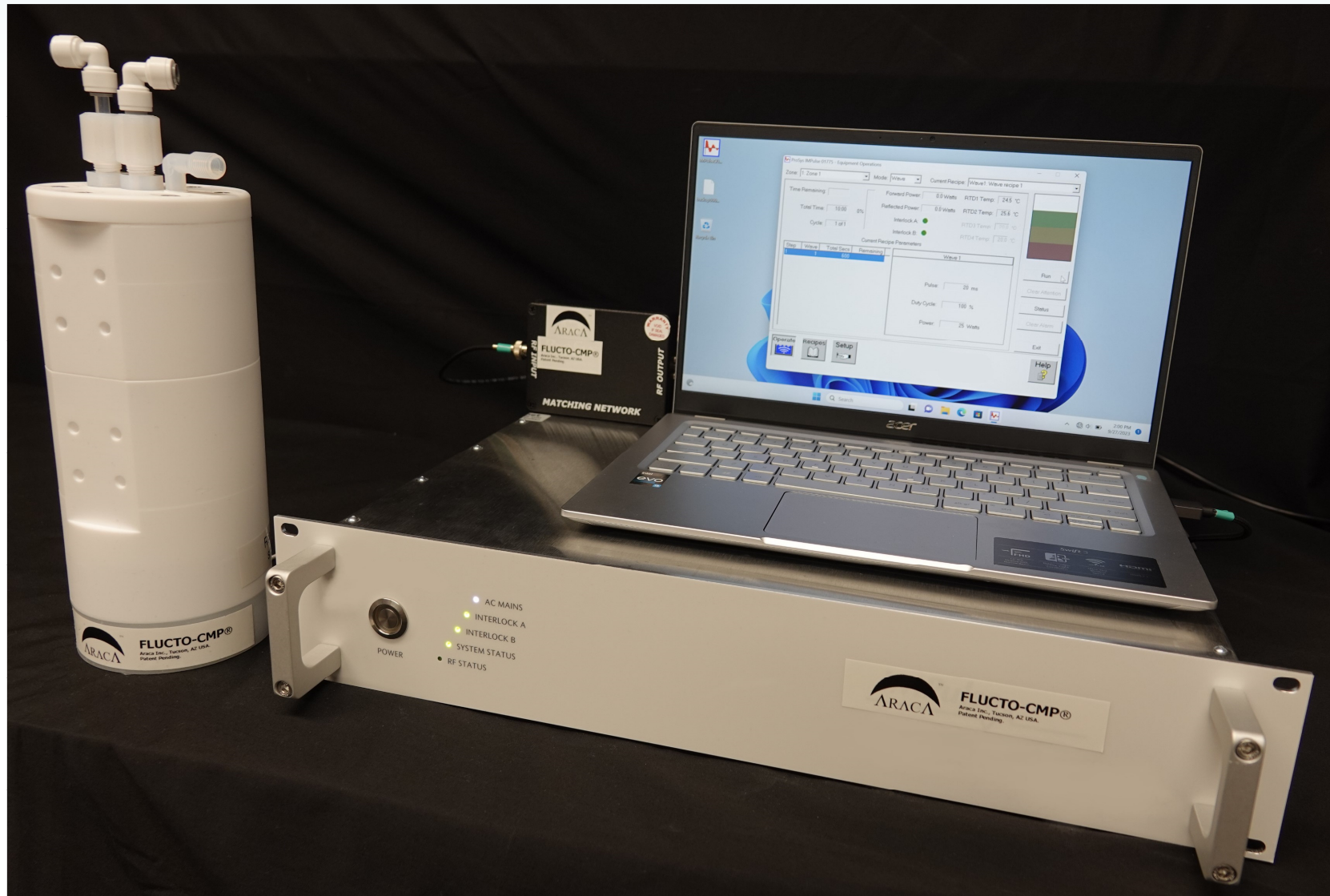


MEGASONIC  
TRANSDUCER

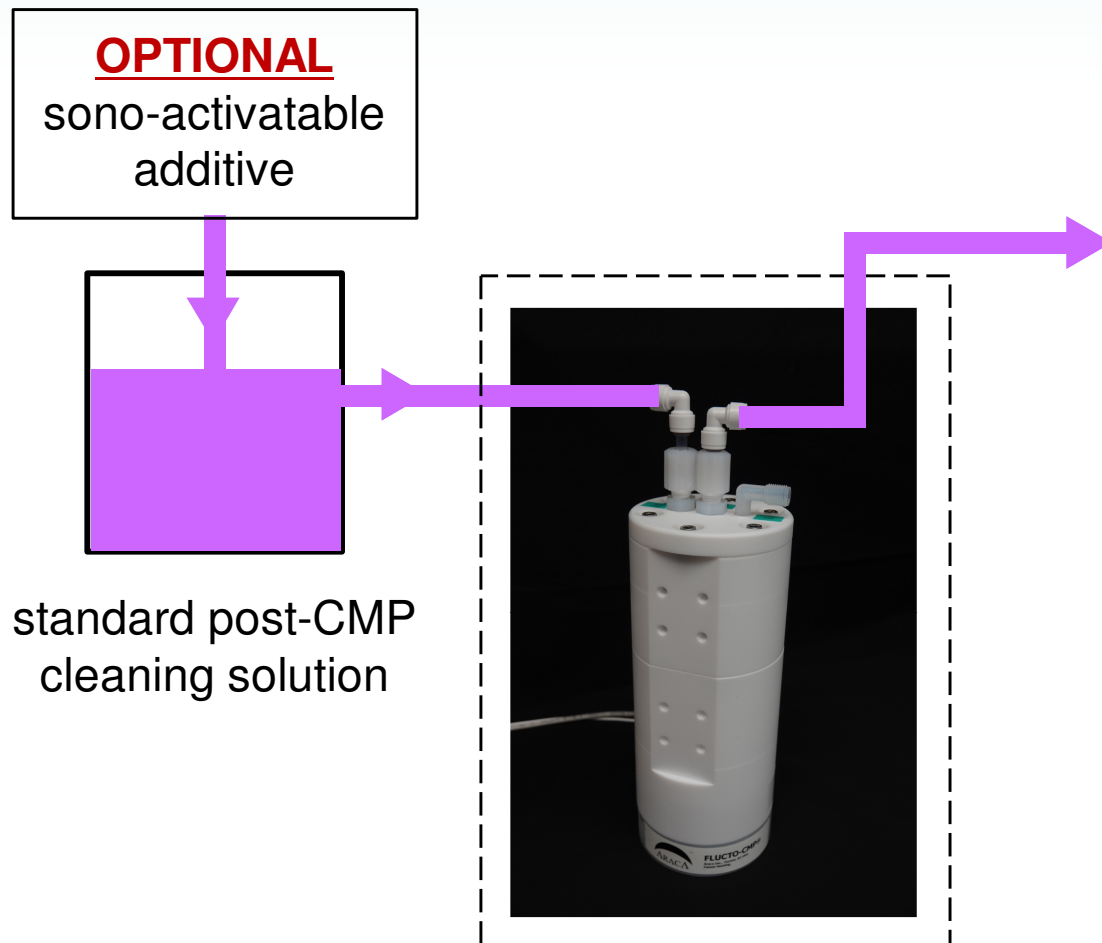
HIGHLY REACTIVE  
AND  
"JAZZED-UP"  
POST-CMP CLEANING  
SOLUTION GOES  
TO THE  
BRUSH SCRUBBER

# The Patent-Pending Flucto-Clean® System by Araca, Inc.

This system, as well as Flucto-CMP®, are co-developed by ProSys (Campbell, CA USA)

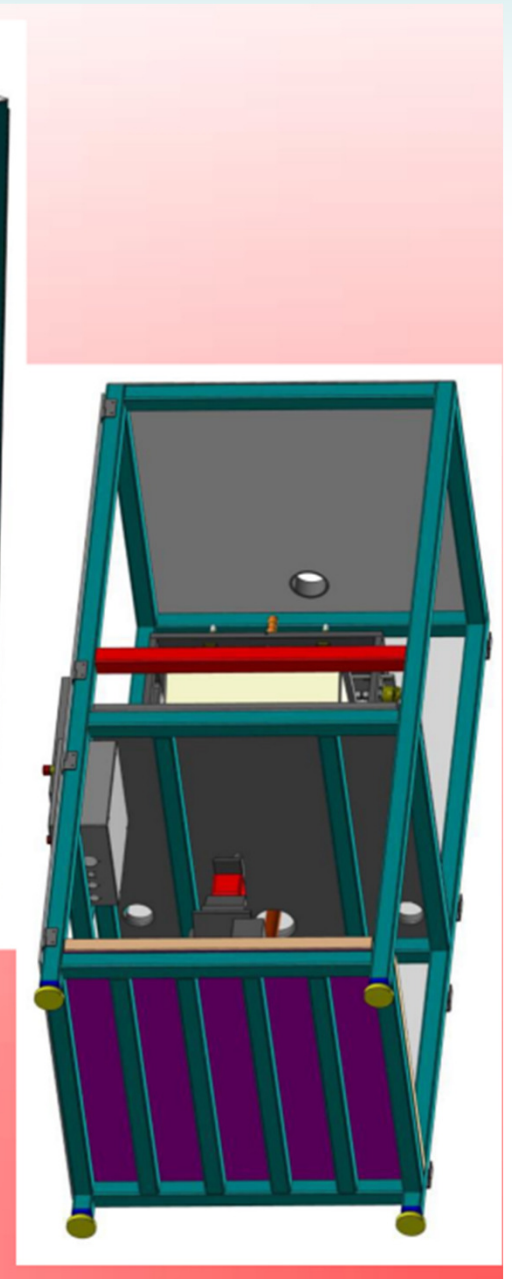
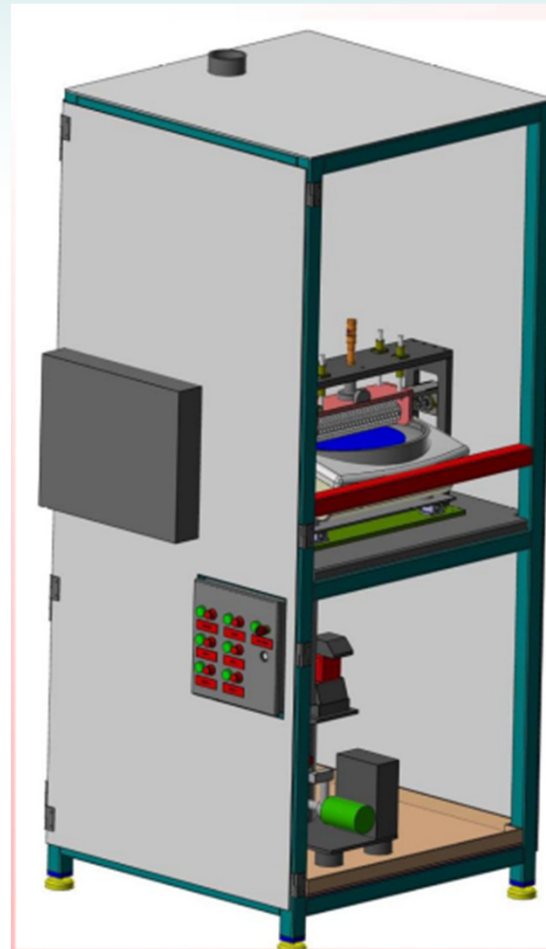
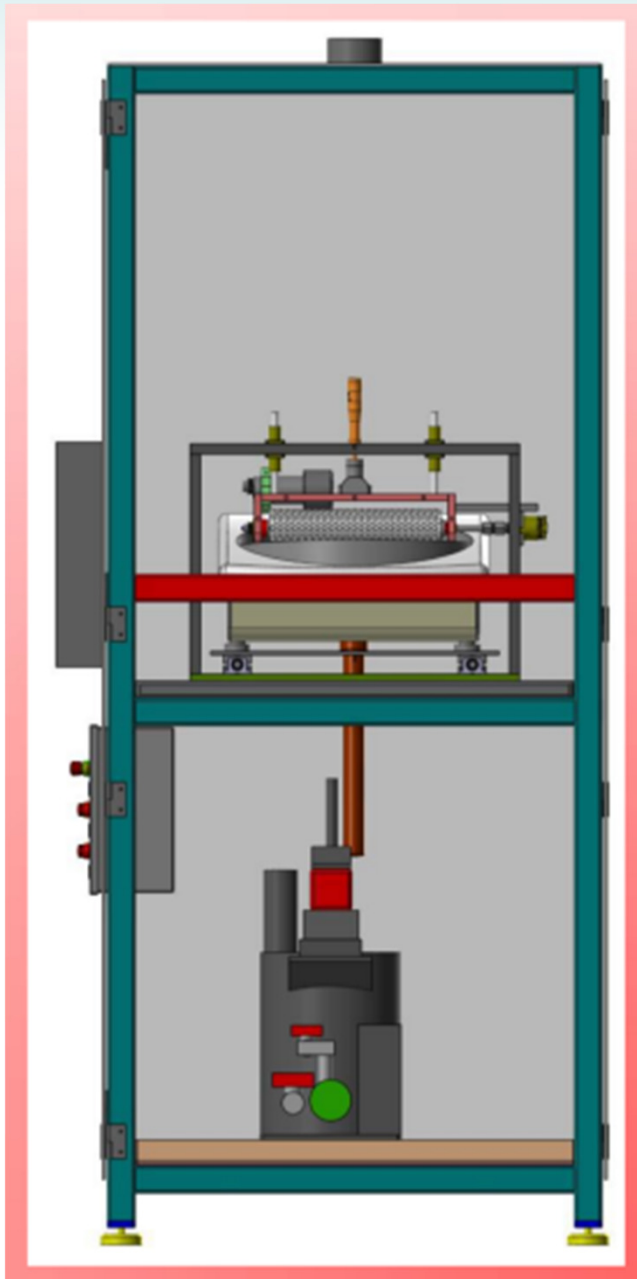


## The Idea Behind Flucto-Clean®

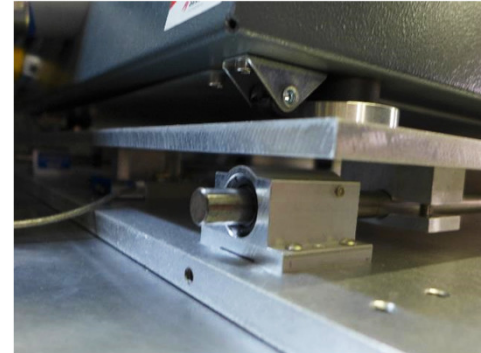
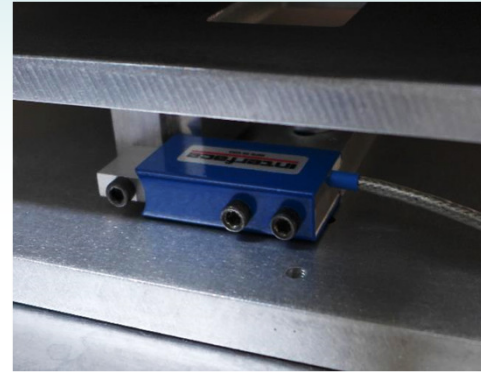
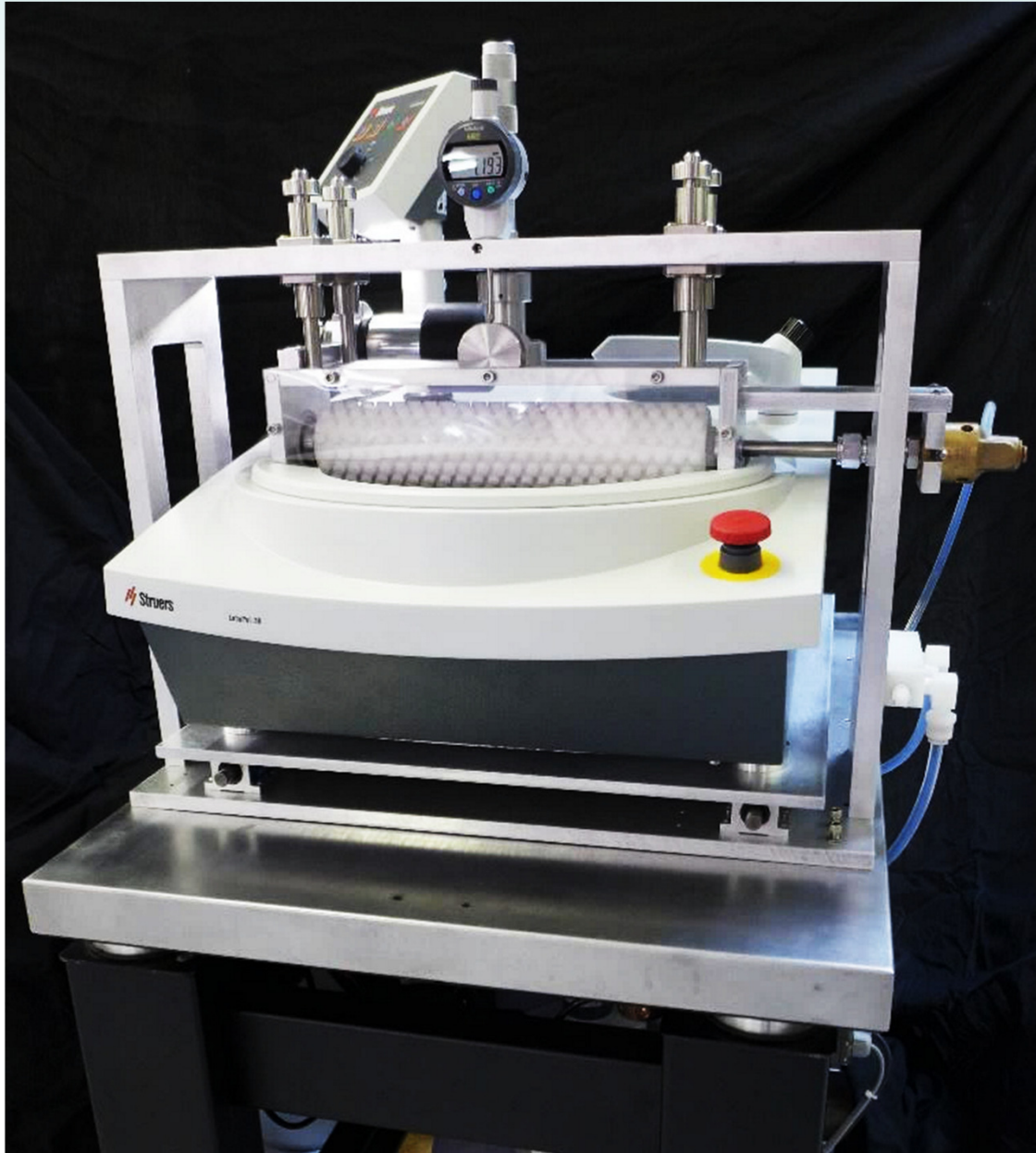


- **Sonication** further activates the chemistry of the cleaning solution and helps create myriad reactive oxidizing species (ROS).
- Dissolved oxygen (DO) in the cleaning solution is enough to initiate the reaction.
- [See proposed mechanism – Slides 12 and 13.](#)
- With optional **sono-activatable additives**, one can control the release of more reactive species which will enhance interfacial kinetics and thermodynamics.
- This results in lower shear forces and an improved particle removal efficiency (PRE).
- [See proposed mechanism – Slides 16 to 18.](#)

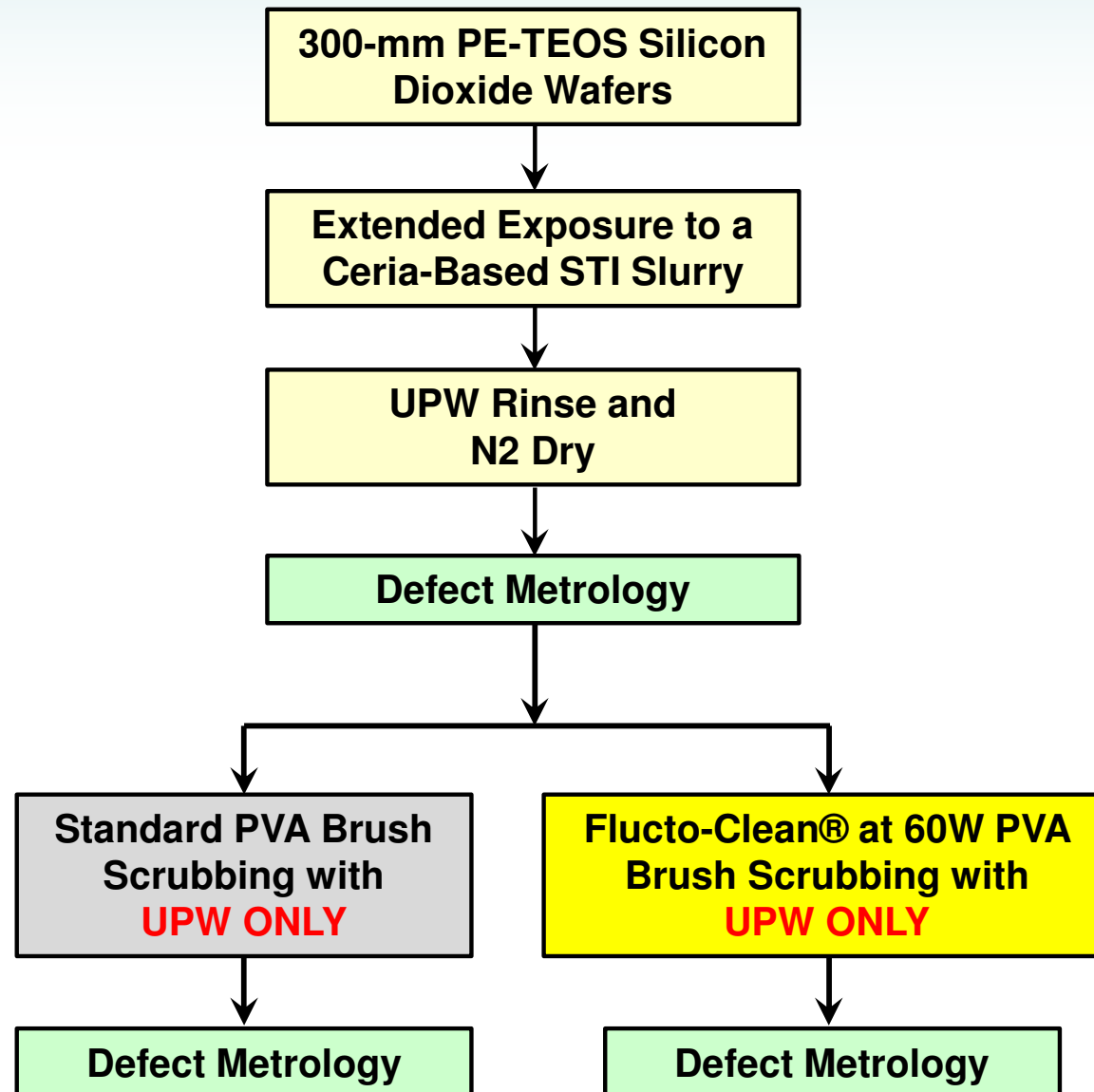
# The Araca PCC-300<sup>®</sup> PVA Scrubber and Tribometer



# The Araca PCC-300<sup>®</sup> PVA Scrubber and Tribometer

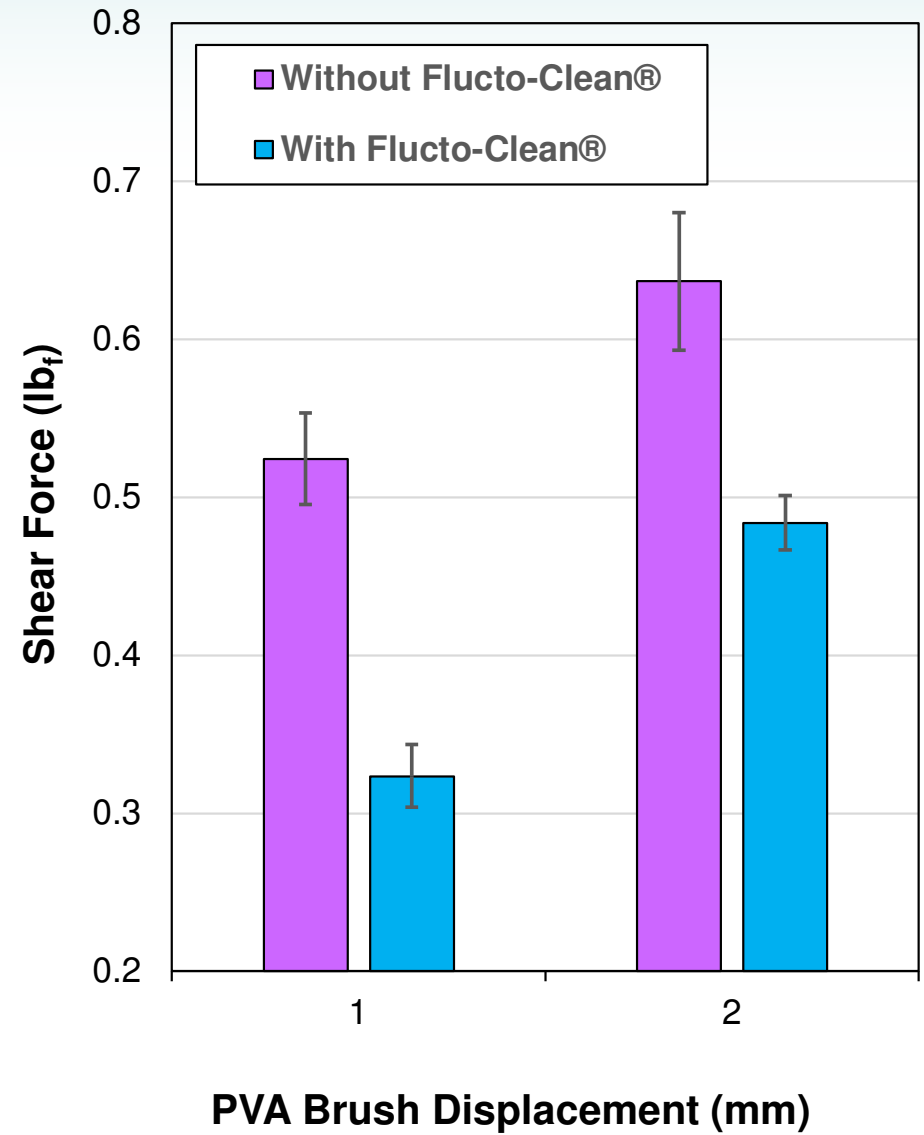
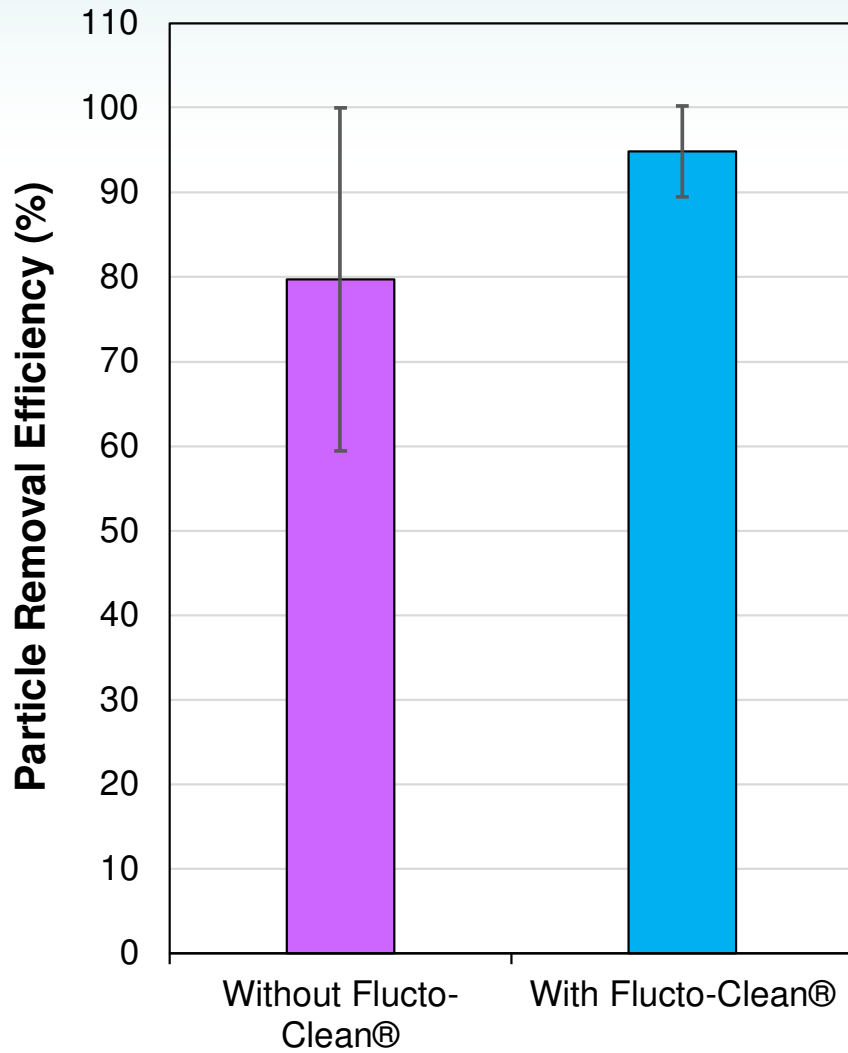


## Example 1 – post-STI-CMP Ceria NP Removal

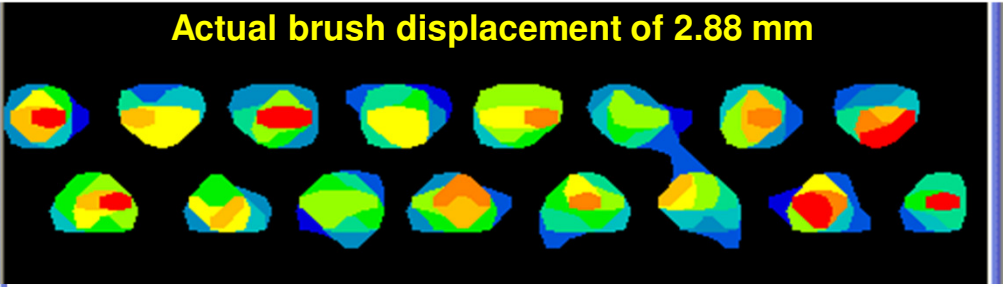
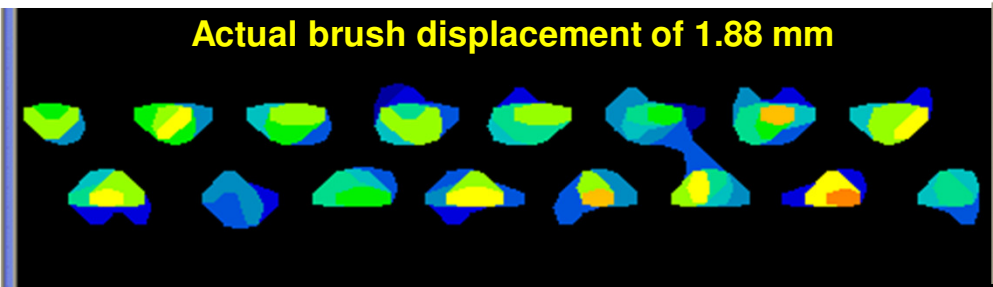
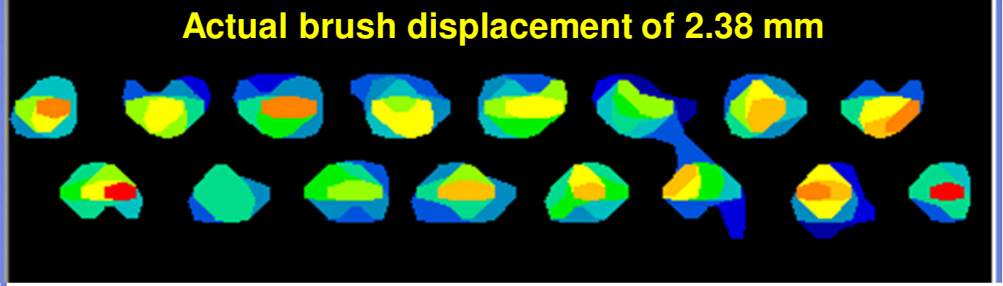
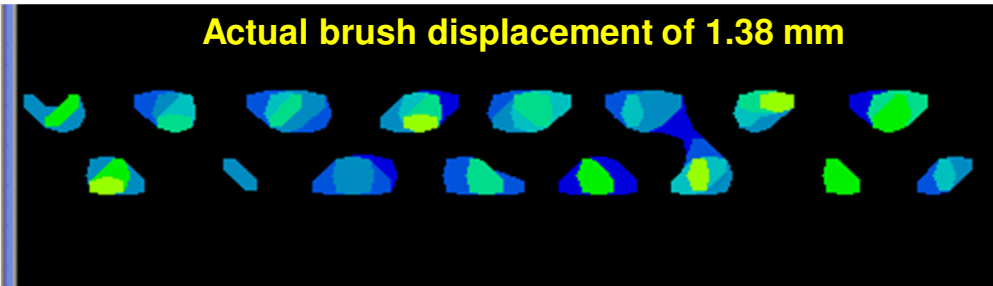
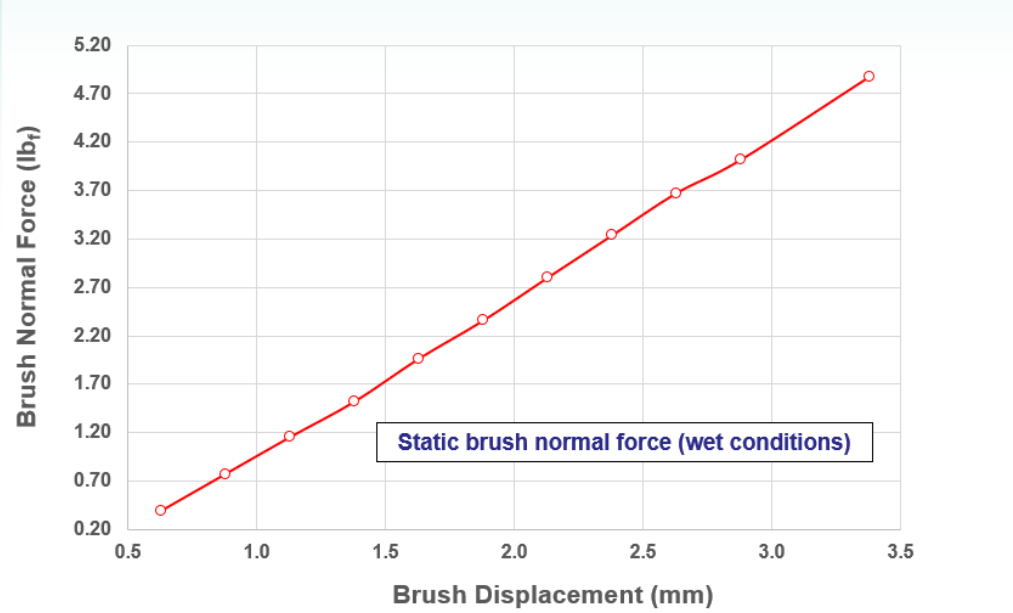
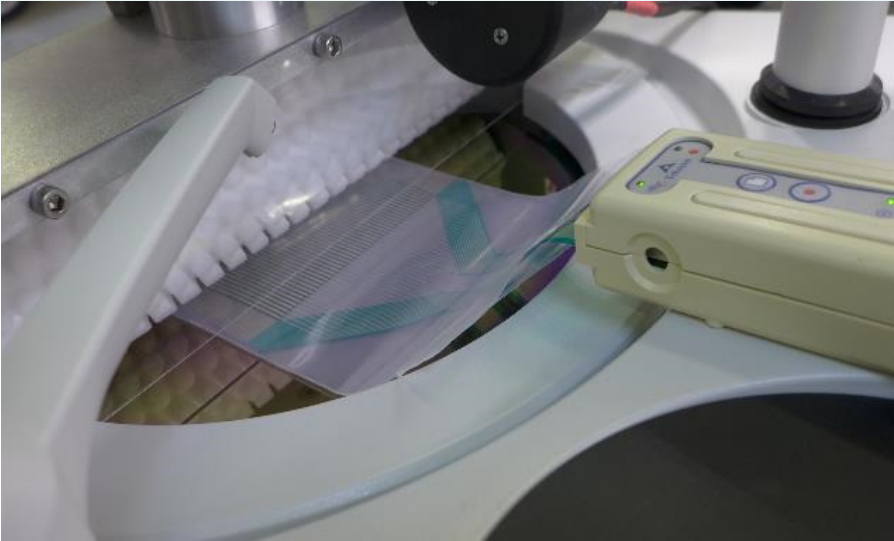




# Example 1 – Ceria NP Removal Efficiency and Shear Forces

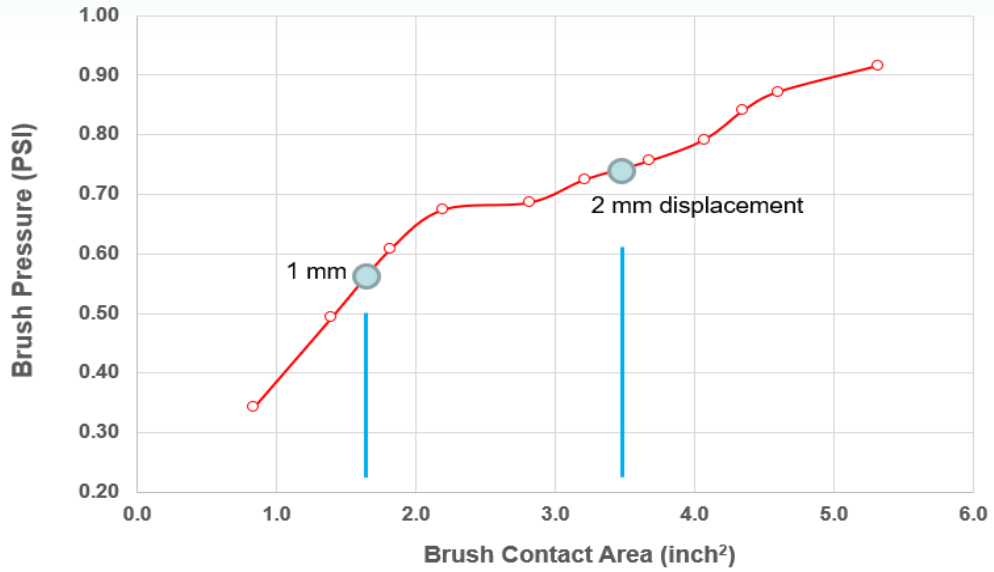
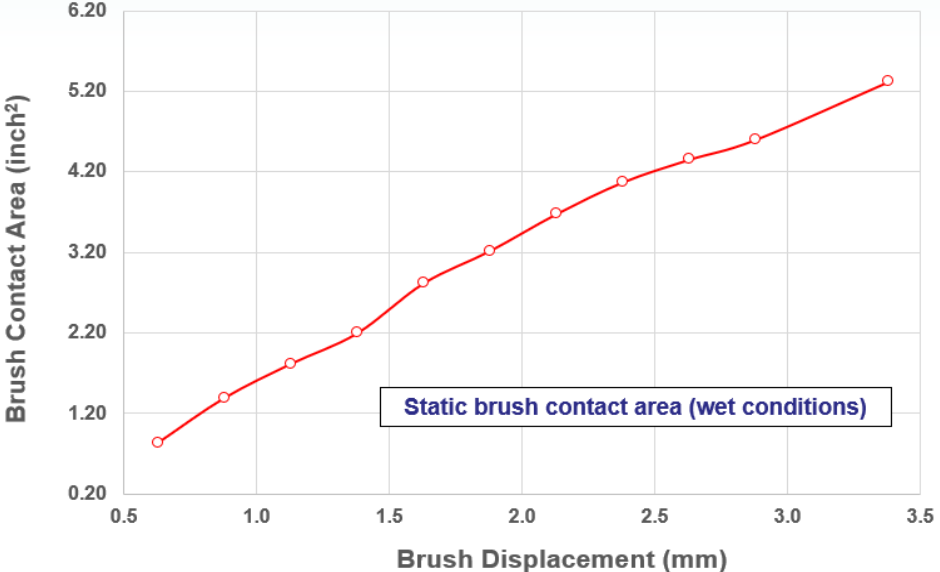
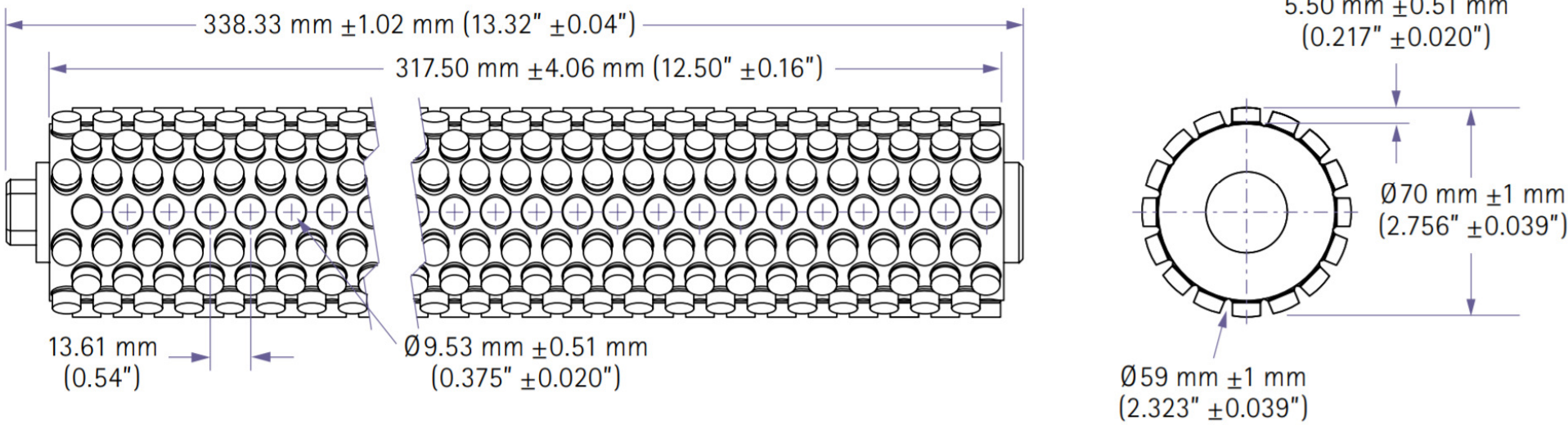


# The Tekscan® Pressure Sensor

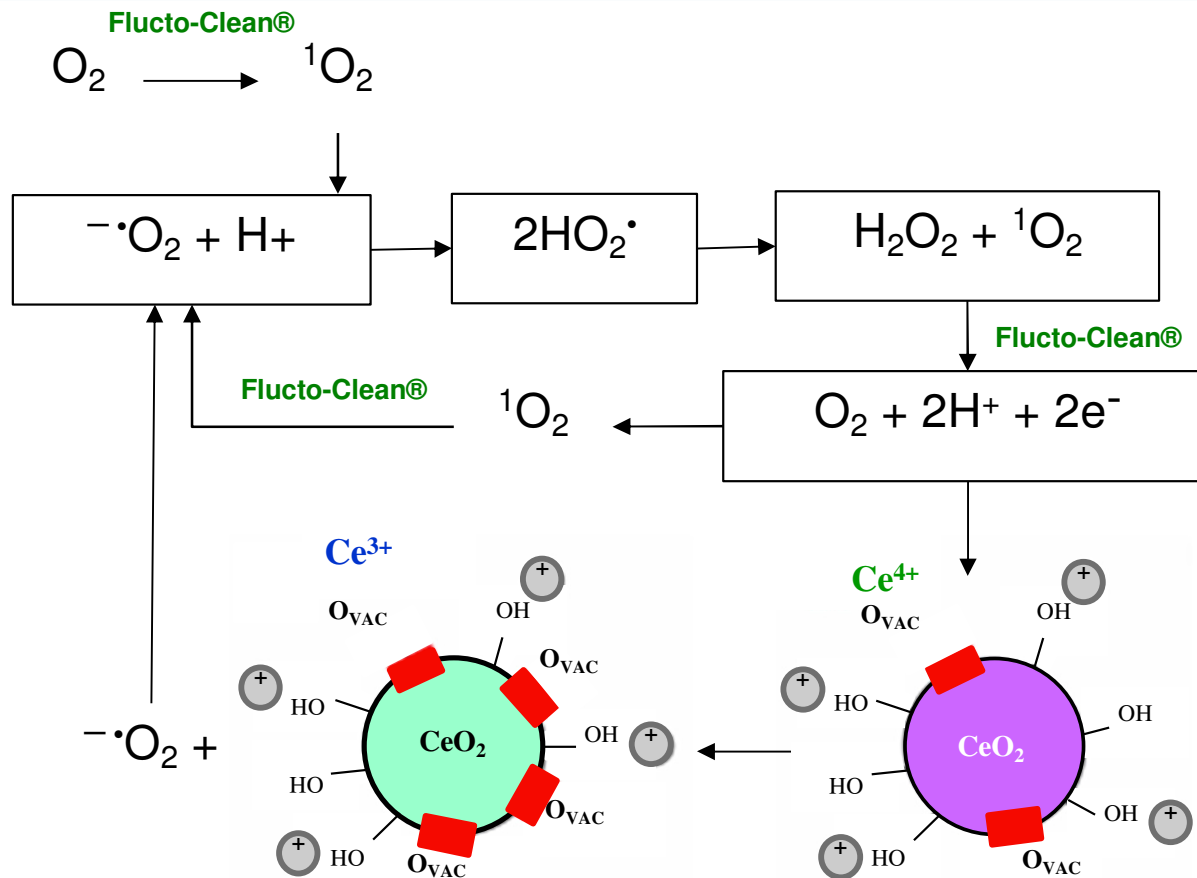


# Area – Pressure – Displacement Relationships

## PVP1ARXR1 and PVPOARXR1 Planarcore Brush

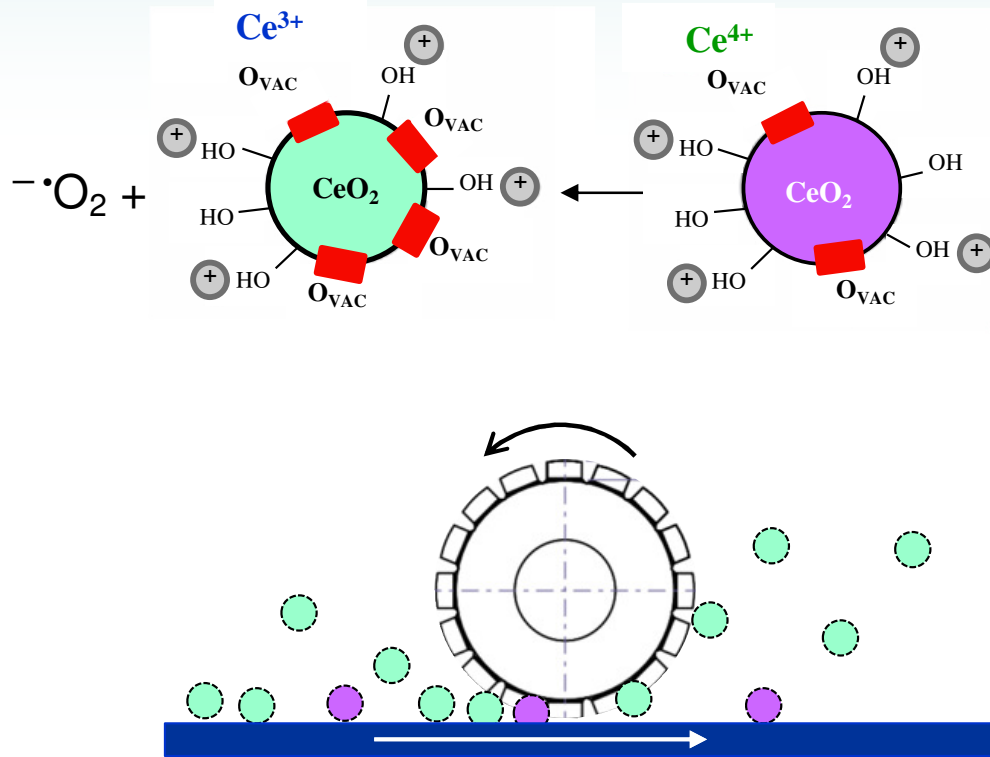


# Example 1 – Proposed Ceria NP Removal Mechanism

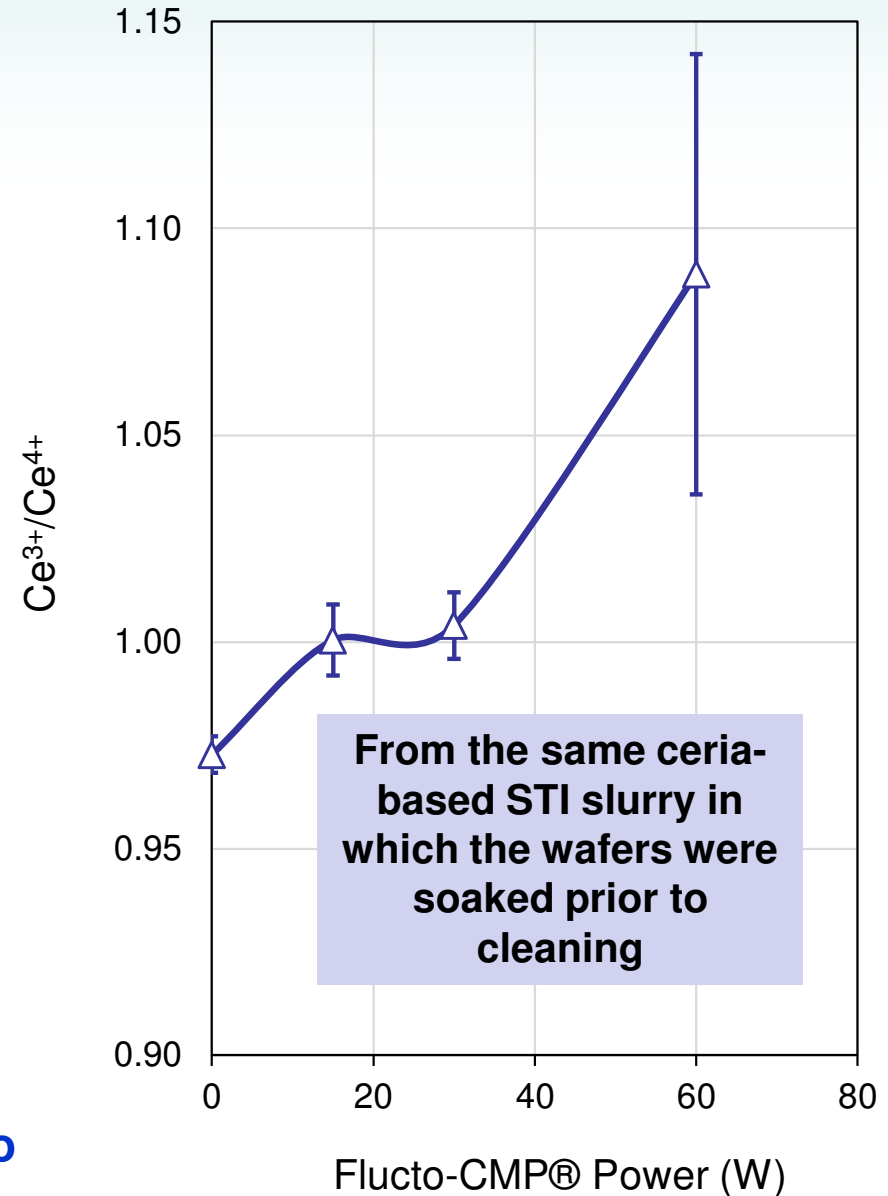


- ✓ With Flucto-Clean® protonation occurs in the presence of DO. This leads to the formation of “peroxo” species ( $H_2O_2$ ).
- ✓ “Peroxo” species degrade in the presence of megasonic energy to form two electrons.
- ✓ The resulting concentration is not significantly high, but the continuously flowing reactor will provide an environment for effective surface reduction of ceria NPs that are present on the wafer.

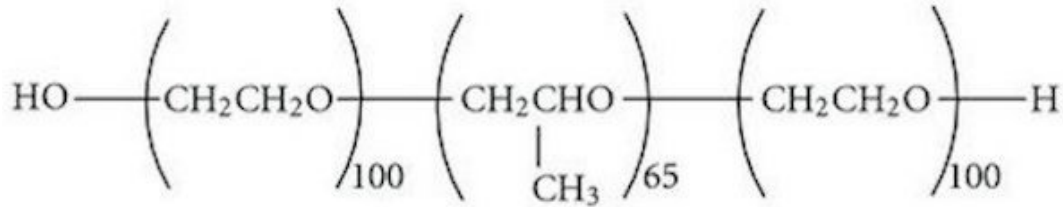
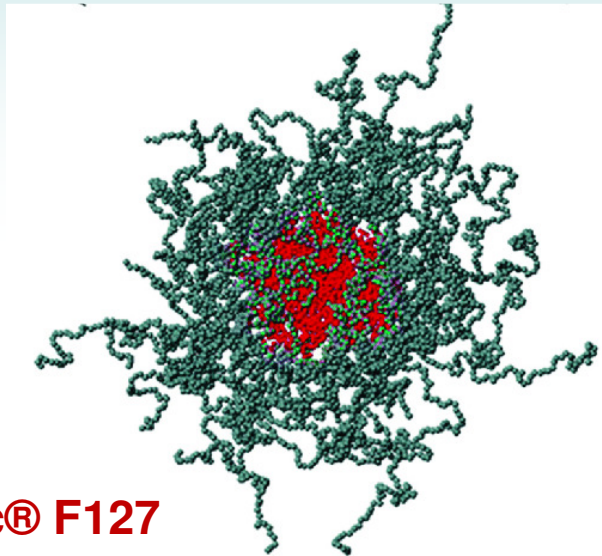
# Example 1 – Proposed Ceria NP Removal Mechanism



The  $\text{Ce}^{4+}$  to  $\text{Ce}^{3+}$  redox reaction weakens the interfacial  $\text{Ce-O-Si}$  bond. This promotes particle removal. This “looser” and “softer” interfacial layer also helps lower the COF.



## Example 2 – SiC post-CMP Alumina NP Removal



100-mm Research Grade Silicon Carbide Wafers

5-minute Polish with KMnO<sub>4</sub> and Alumina NP Slurry

UPW Rinse and N<sub>2</sub> Dry

Defect Metrology

Standard PVA Brush Scrubbing with **UPW ONLY**

Defect Metrology

Standard PVA Brush Scrubbing with **UPW and F127**

Defect Metrology

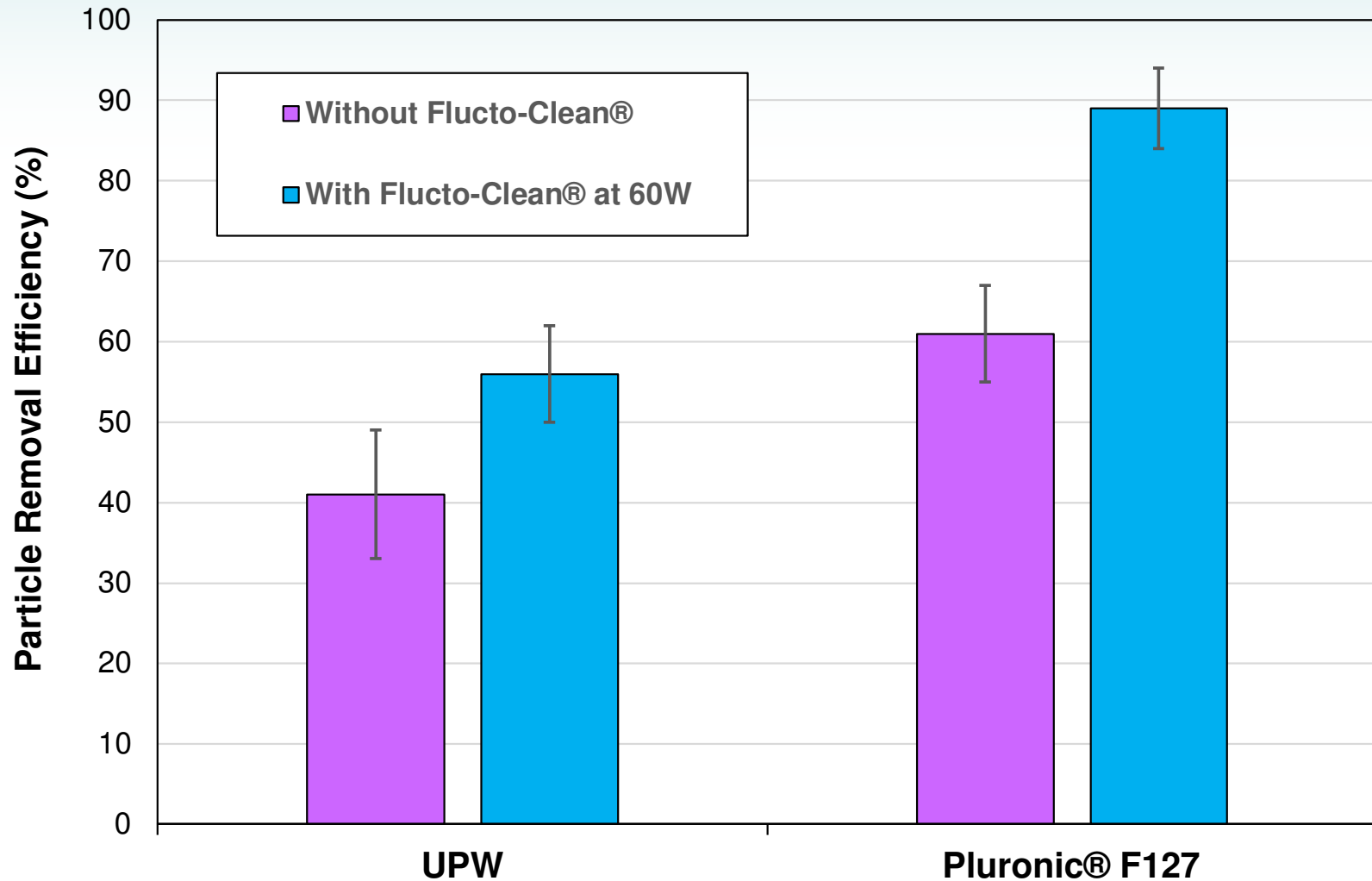
Flucto-Clean® at 60W PVA Brush Scrubbing with **UPW ONLY**

Defect Metrology

Flucto-Clean® at 60W PVA Brush Scrubbing with **UPW and F127**

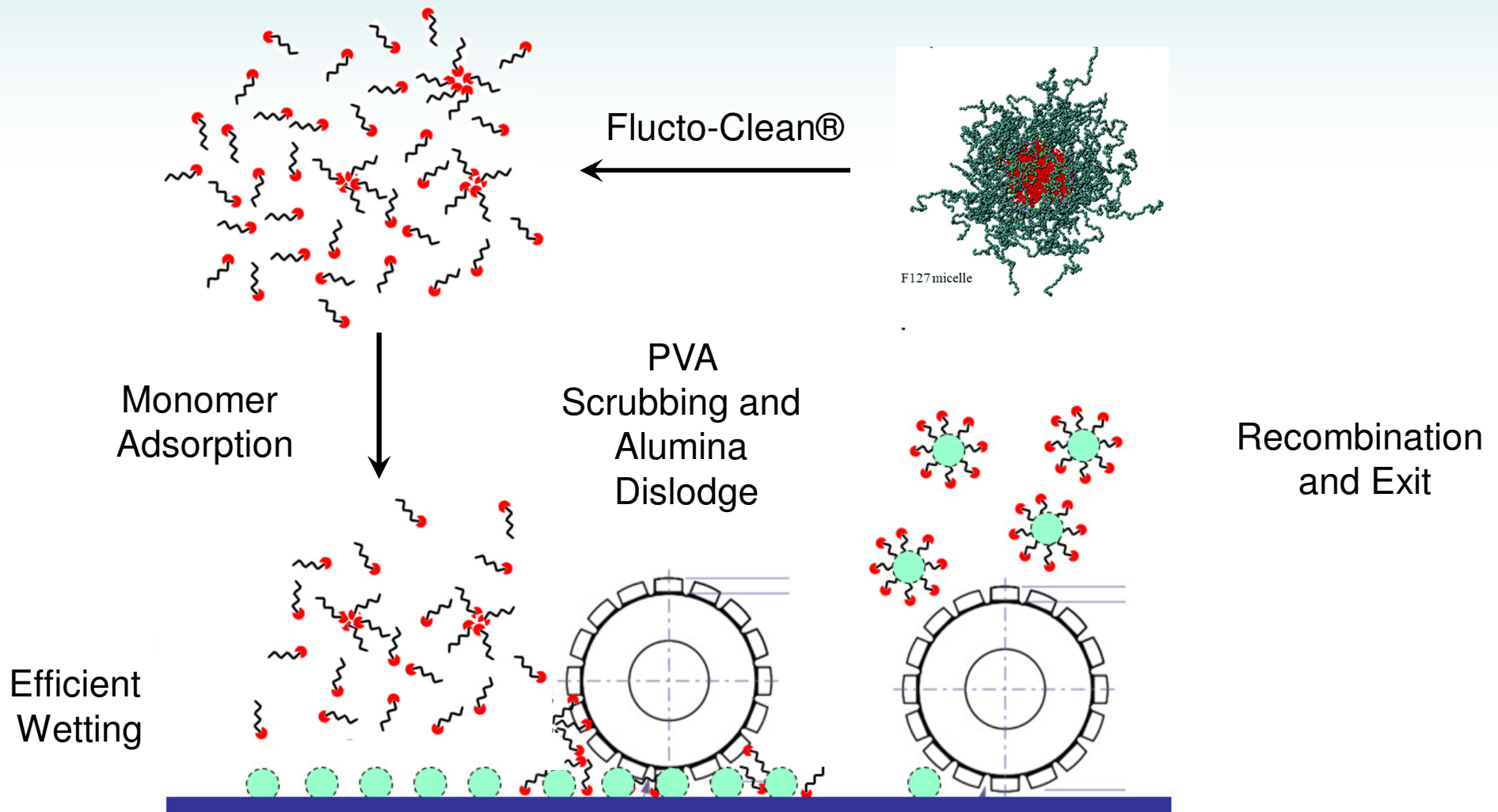
Defect Metrology

## Example 2 – Post-SiC-CMP Alumina NP Removal Data with F127



In all 4 cases, EDX analysis of carbon residue on the SiC wafers showed no change in carbon levels compared to the reference wafer (essentially below detection limits).

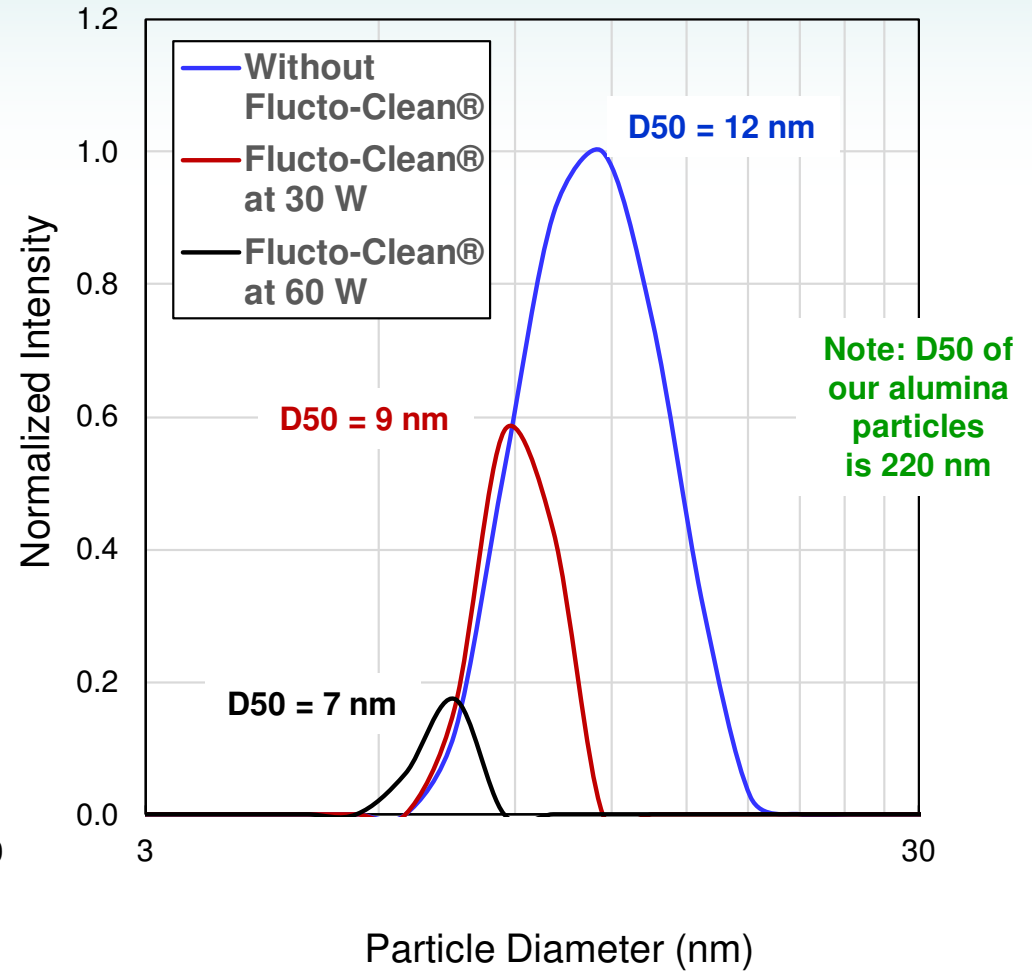
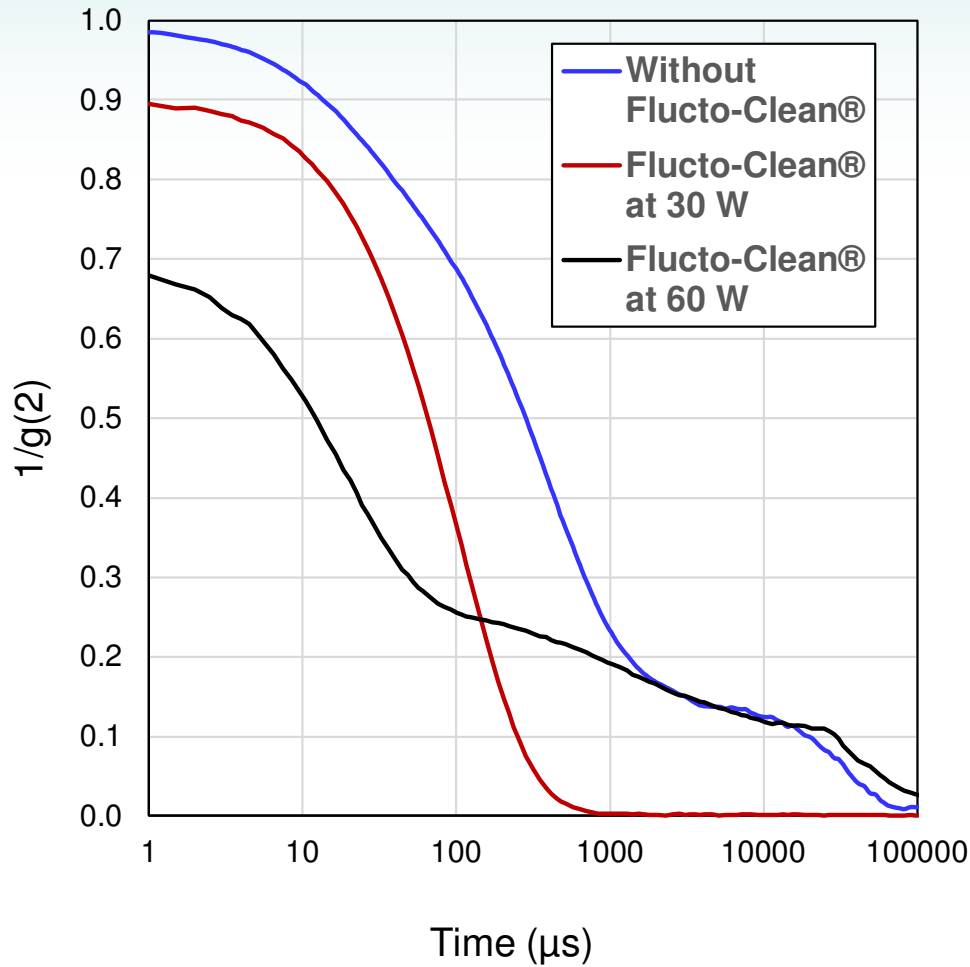
# Proposed Mechanism – Pluronic® F127 with Flucto-Clean®



**F127** is a micellar surfactant. We postulate that there is **breaking of micelles into monomers** due to sonic waves prompted by Flucto-Clean®. At the wafer-brush interface, the removal of dislodged alumina particles is facilitated via recombination with the F127 monomers that also **promote wetting**.



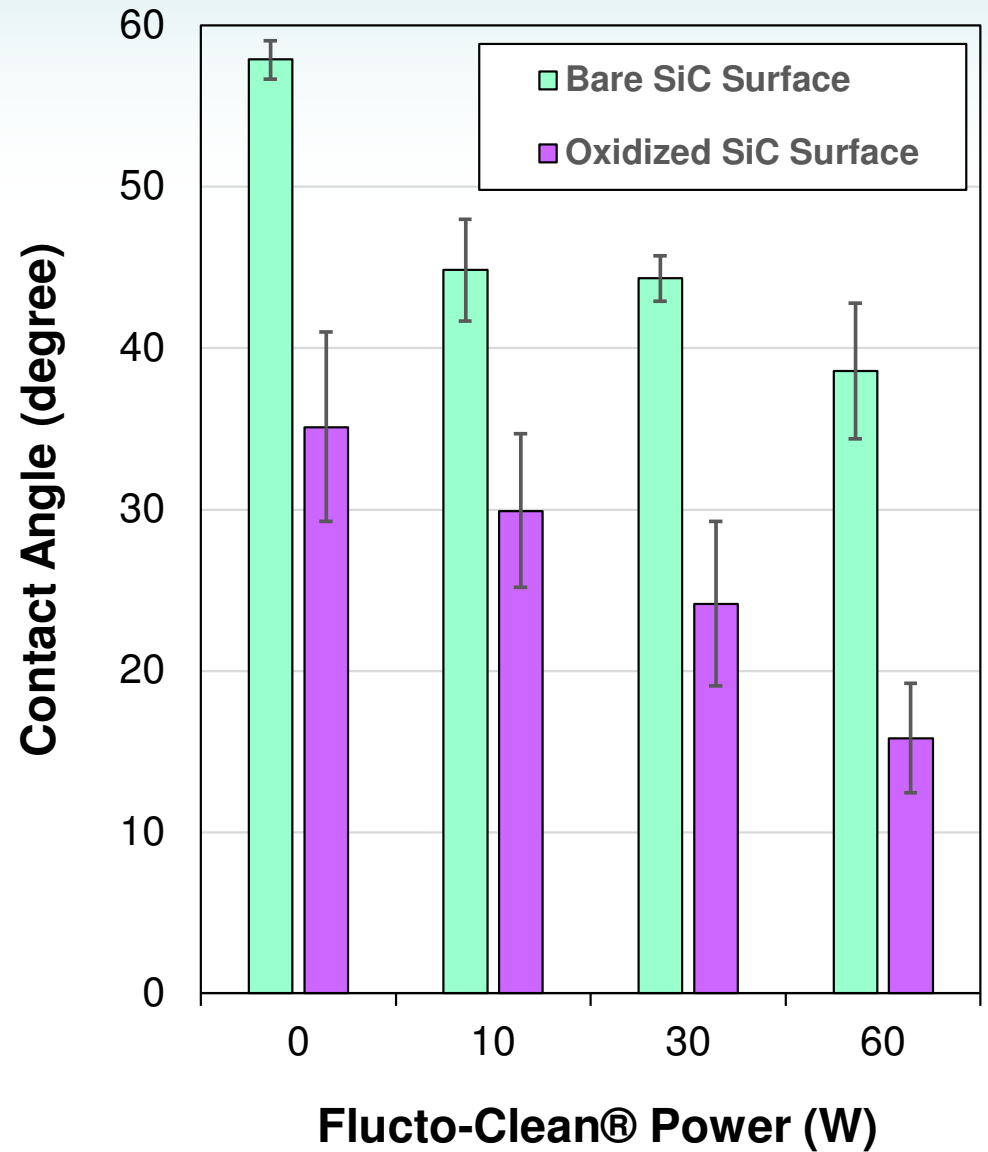
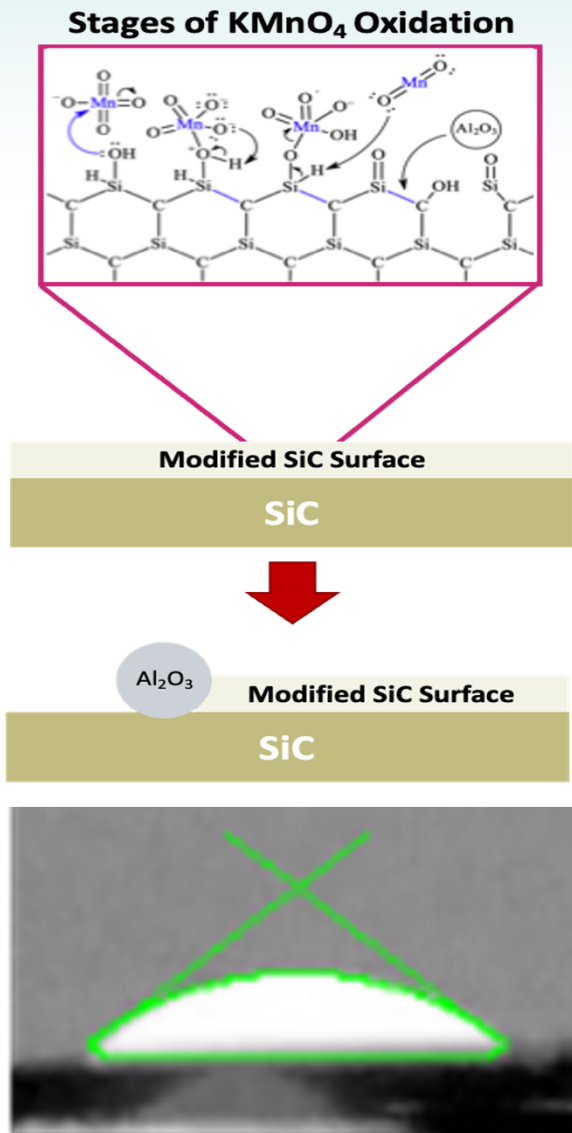
# Proof of Micellar Fracture into Smaller Micelles and Monomers



Photon Correlation Spectra re:  
F127 – Malvern Zetasizer Nano ZS

Stokes – Einstein Equation

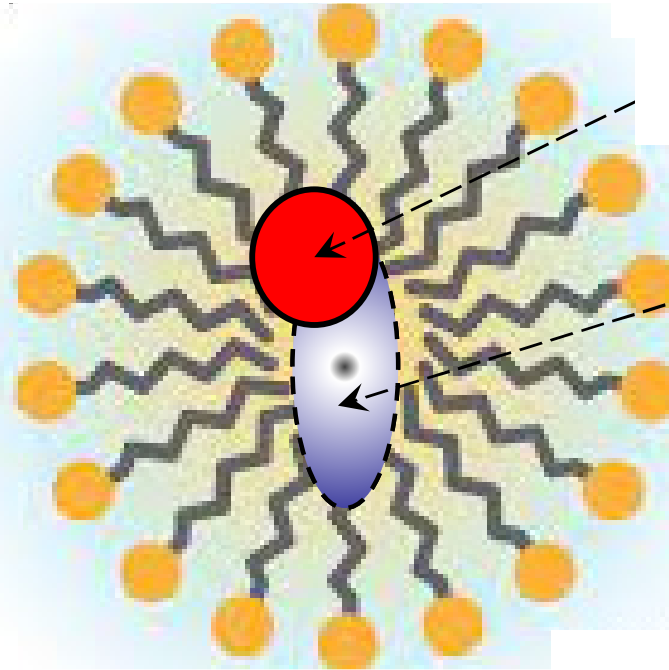
# Wetting Characteristics of F127 Micelles and Monomers



Analyzing the Air – SiC – F127 contact angle on bare and oxidized wafers

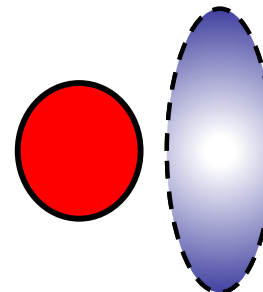
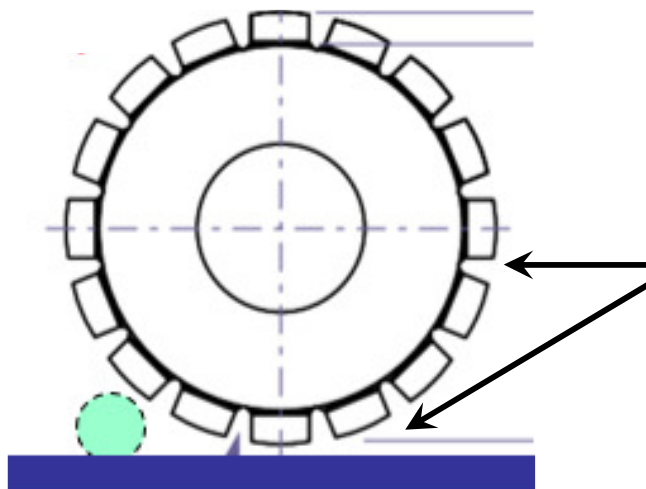
## Another Approach – Looking for a JDP Partner

Supramolecular shell surfactants allow one to introduce non-soluble chemicals into the solution



Non-soluble cleaning rate enhancer

Non-soluble Non-metallic ROS catalyst



**Flucto-Clean® will break apart the micellar supramolecule and release the active chemicals**

## Summary

- The patent-pending Flucto-Clean® system is showing promise.
- With up-stream sonication in post-STI-cleaning, we can activate the chemistry of the cleaning solution. This creates myriad reactive oxygen species (ROS):
  - ❖ Improved PRE and results in tighter distributions.
  - ❖ Lowers shear forces (we don't yet know how this has come about, but are working to understand its fundamentals).
  - ❖ Lowers surface tension.
- In the case of post-SiC-clean, with sono-activatable additives (Pluronic® F127), we can enhance interfacial kinetics and thermodynamics to improve PRE.
- We are starting to use Flucto-Clean® to break apart new additives inside the cleaning solutions (such as micellar supramolecules) to release the active chemicals that we have embedded inside them.

**We are looking for a JDP partner who can make and sell post-CMP cleaning chemicals. Please contact me offline!**



**The Premier Provider of Services and Equipment to the Semiconductor  
Polishing and Planarization Industries**

**Thank You!**

